

100V N-Channel Power MOSFET

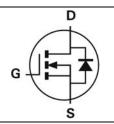
V_{DSS}, 100V

 $R_{DS(ON)}$, $26m\Omega$ (max.) @ V_{GS}=10V $R_{DS(ON)}$, $31m\Omega$ (max.) @ V_{GS}=4.5V

I_D , 9.8A







Description

The SG100N03S uses advanced Trench technology and designs to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- · Low On-Resistance
- Low Input Capacitance
- Low Miller Charge
- Low Input/Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG100N07S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
T _A =25°C			8.3	Α
Drain Current-Continuous	T _A =75°C	ID ID	6.4	Α
Drain Current-Pulsed Note 1		I _{DM}	34	Α
Avalanche Current, L=0.1mH		las	15	Α
Avalanche Energy, L=0.1mH		Eas	11	mJ
Maximum Power Dissipation	T _A =25°C	P _D	2.9	W
Maximum Fower Dissipation	T _A =75°C	FD	1.7	W
Storage Temperature Range		Tstg	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	Reja	Steady-State	=	43.5	=	°C/W
Thermal Resistance, Junction-to-Case	Rejc	Steady-State	-	11.4	-	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	В	V _{GS} =10V, I _{DS} =10A	-	-	26	mΩ
	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =6A	-		31	
Gate Resistance	Rg	V _{GS} =0V, f=1MHz	-	0.45	1	Ω

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{iss}		-	3210	-	
Output Capacitance	Coss	V _{DS} =50V, V _{GS} =0V, f=1MHz	7	97	-	pF
Reverse Transfer Capacitance	Crss		-	55	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	12.4	-	
Rise Time	tr	V_{GS} =10V, V_{DS} =50V, R_L =2.5 Ω ,	-	26.8	-	
Turn-Off Delay Time	T _{d(off)}	R _{GEN} =3Ω	-	35.1	-	ns
Fall Time	t _f		-	24	-	
Total Gate Charge at 10V	Qg		-	59	-	
Gate to Source Gate Charge	Qgs	V _{GS} =10V, V _{DS} =50V, I _D =20A	-	14.8	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	9.5	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =10A	-	-	1.3	V
Body Diode Reverse Recovery Time	trr	t _{rr}		23	-	ns
Body Diode Reverse Recovery Charge	Qrr	l _F =20A, dl/dt=100A/μs	-	27	-	nC

Notes:

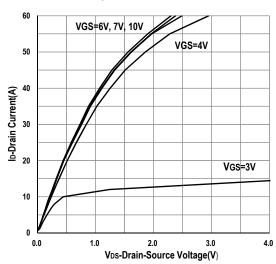
- 1. Pulse Test: Pulse Width ≤ 10ms, Duty Cycle ≤ 1%.
- 2. For surface-mounted devices, both R_{BCA} and R_{BJC} are measured with the device mounted on approximately 1"×1" FR-4 PCBs. In actual applications, many factors including the PCB material and layout, may affect the thermal resistance of the device-board assembly. For best results, characterize the thermal resistance directly in the application circuit.



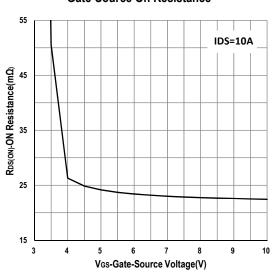
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Typical Operating Characteristics

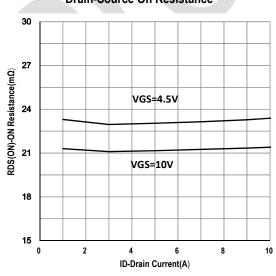




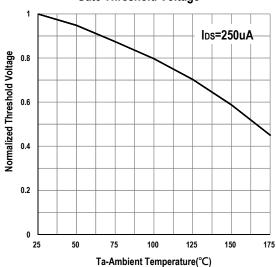
Gate-Source On Resistance



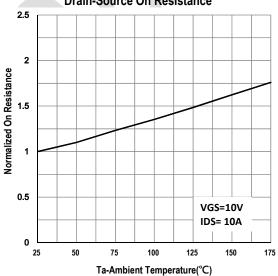
Drain-Source On Resistance



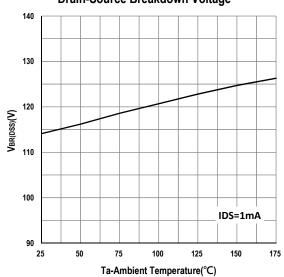
Gate Threshold Voltage



Drain-Source On Resistance



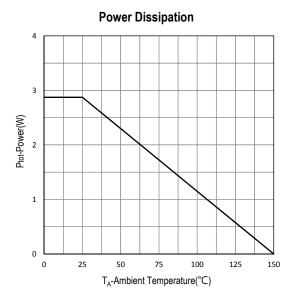
Drain-Source Breakdown Voltage



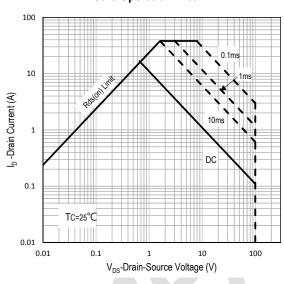


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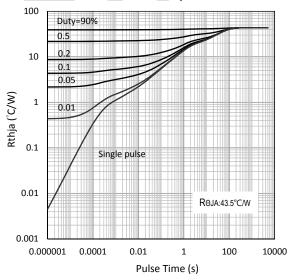
Typical Operating Characteristics (Cont.)



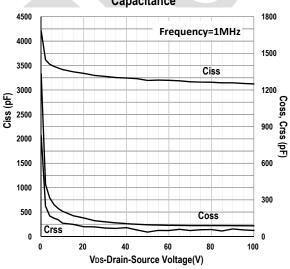




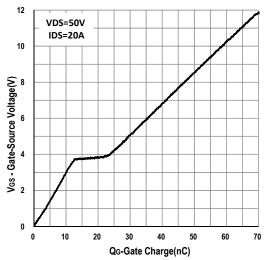




Capacitance



Gate Charge



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Marking Information

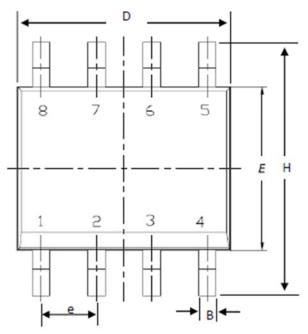
SOP-8	Marking Rule	
SOP-8 Laser Marking SG100N07S YYMMXXX	Line 1 : Device Name SG100N07S Line 2 : Date Code YYMMXXX YY : Year Code	
	MM : Month Code XXX : Serial Number	



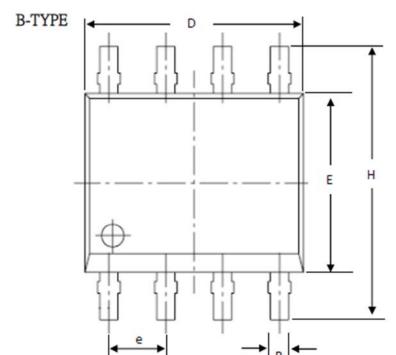
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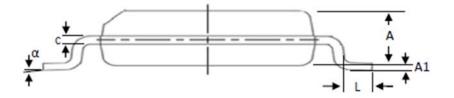
Package of Dimension





Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
е	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00





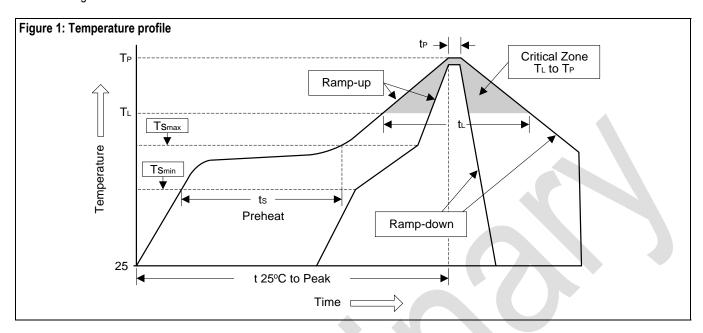
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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		,
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t _P)	10 to 30 sec	20 to 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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